



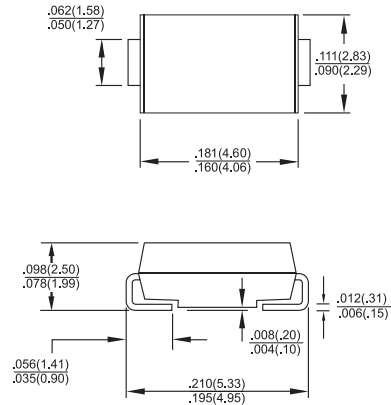
### Features

- ✧ For surface mounted application
- ✧ Glass passivated junction chip.
- ✧ Low forward voltage drop
- ✧ High current capability
- ✧ Easy pick and place
- ✧ High surge current capability
- ✧ Plastic material used carries Underwriters Laboratory Classification 94V-0
- ✧ High temperature soldering: 260°C / 10 seconds at terminals
- ✧ High reliability grade (AEC Q101 qualified)

### Mechanical Data

- ✧ Case: Molded plastic
- ✧ Terminals: Pure tin plated, lead free solderable per J-STD-002B and JESD22-B102D.
- ✧ Polarity: Indicated by cathode band
- ✧ Packaging: 12mm tape per EIA STD RS-481
- ✧ Weight: 0.064 gram

### SMA/DO-214AC



Dimensions in inches and (millimeters)

### Maximum Ratings and Electrical Characteristics

Rating at 25 °C ambient temperature unless otherwise specified.  
 Single phase, half wave, 60 Hz, resistive or inductive load.  
 For capacitive load, derate current by 20%

Type Number	Symbol	M1X	M2X	M3X	M4X	M5X	M6X	M7X	Units	
Maximum Recurrent Peak Reverse Voltage	$V_{RRM}$	50	100	200	400	600	800	1000	V	
Maximum RMS Voltage	$V_{RMS}$	35	70	140	280	420	560	700	V	
Maximum DC Blocking Voltage	$V_{DC}$	50	100	200	400	600	800	1000	V	
Maximum Average Forward Rectified Current @ $T_L = 110^\circ C$	$I_{(AV)}$	1.0							A	
Peak Forward Surge Current, 8.3 ms Single Half Sine-wave Superimposed on Rated Load (JEDEC method )	$I_{FSM}$	40							30	A
Maximum Instantaneous Forward Voltage @ 1.0A	$V_F$	1.1							V	
Maximum DC Reverse Current @ $T_A = 25^\circ C$ at Rated DC Blocking Voltage @ $T_A = 125^\circ C$	$I_R$	5.0 50							$\mu A$ $\mu A$	
Typical Reverse Recovery Time (Note 1)	$T_{rr}$	1.5							$\mu S$	
Typical Junction Capacitance ( Note 2 )	$C_j$	12							pF	
Non-Repetitive Peak Reverse Avalanche Energy at 25°C, $I_{AS}=1A$ , $L=10mH$	$E_{AS}$	5							mJ	
Typical Thermal Resistance (Note 3)	$R_{\theta JL}$ $R_{\theta JA}$	27 75							30 85	$^\circ C/W$
Operating Temperature Range	$T_J$	-55 to +150							$^\circ C$	
Storage Temperature Range	$T_{STG}$	-55 to +150							$^\circ C$	

- Notes:
1. Reverse Recovery Test Conditions:  $I_F=0.5A$ ,  $I_R=1.0A$ ,  $I_{RR}=0.25A$
  2. Measured at 1 MHz and Applied  $V_r=4.0$  Volts
  3. Measured on P.C. Board with 0.2" x 0.2" (5.0mm x 5.0mm) Copper Pad Areas.



#### RATINGS AND CHARACTERISTIC CURVES (M1 THRU M7X)

FIG.1- MAXIMUM FORWARD CURRENT DERATING CURVE

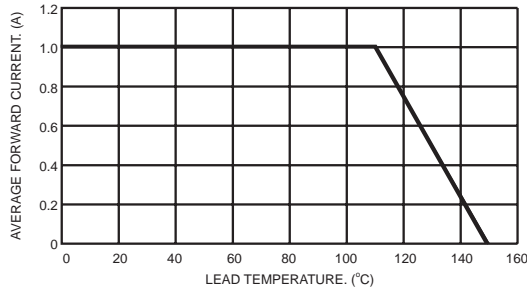


FIG.2- TYPICAL REVERSE CHARACTERISTICS

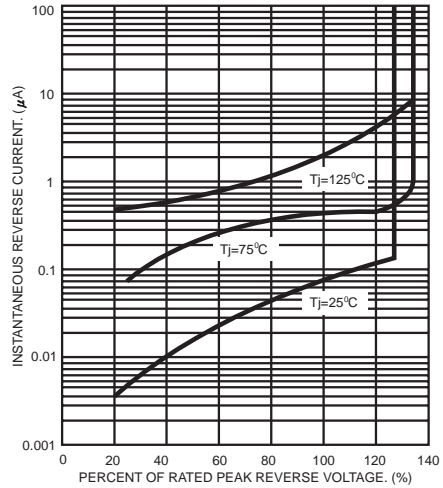


FIG.3- MAXIMUM NON-REPETITIVE FORWARD SURGE CURRENT

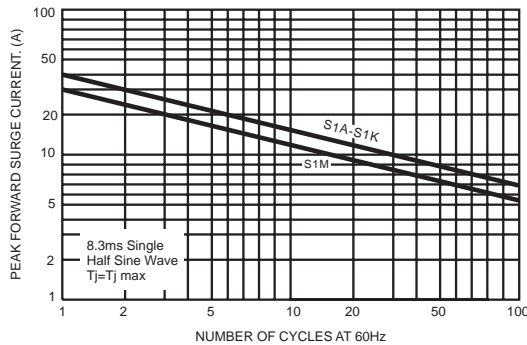


FIG.5- TYPICAL FORWARD CHARACTERISTICS

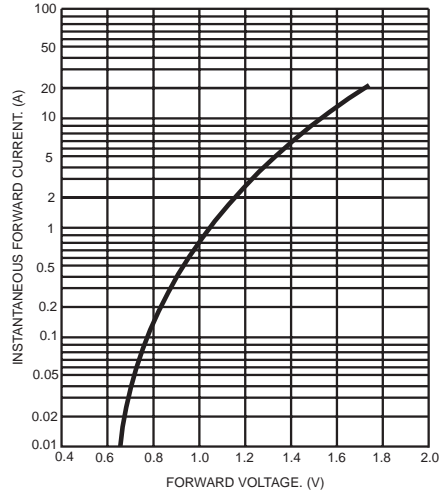


FIG.4- TYPICAL JUNCTION CAPACITANCE

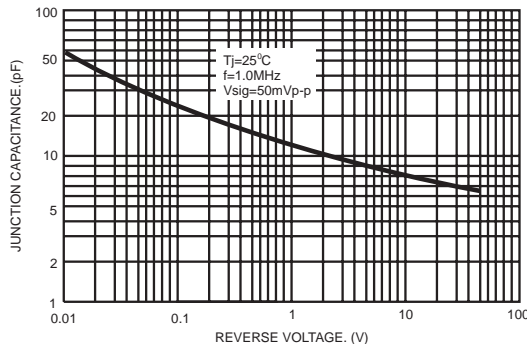
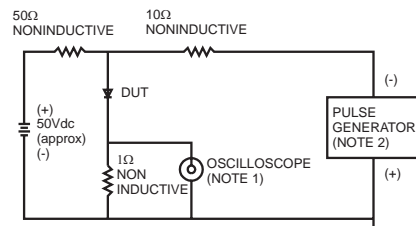
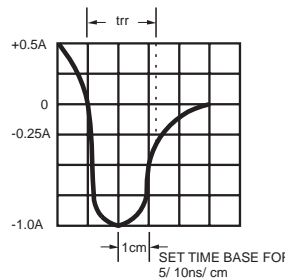


FIG.6- REVERSE RECOVERY TIME CHARACTERISTIC AND TEST CIRCUIT DIAGRAM



NOTES: 1. Rise Time=7ns max. Input Impedance=1 megohm 22pf  
 2. Rise Time=10ns max. Source Impedance=50 ohms



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